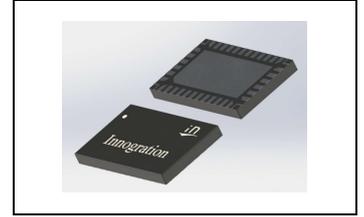




5.9-6.1GHz, 35W, 50V GaN fully matched PA Module

Description

The SMAV5961-35 is a 35-watt, integrated 2-stage Power Amplifier Module, designed for 5G massive MIMO applications, with frequencies from 5.9 to 6.1GHz. The module is 50 Ω input and output fully matched, and requires minimal external components. The module offers a much smaller footprint than traditional discrete component solutions, with much less sensitivity for production, housed in 10*6mm cost effective plastic open cavity package. The module incorporates a Doherty circuit delivering high power added efficiency for the entire module at 5.6 average power.



Innegration owns the patents for internal Doherty architecture, and related plastic open cavity.

• Typical 1 Carrier WCDMA Performance of Doherty Demo (On Innegration fixture with device soldered):

| VDS= 50V, Idq1=10mA, Idq2=22mA, Vpeak=-4.9V | | | | |
|---|------------|------------|-----------|---------|
| Pout=37.5dBm | | | | |
| Freq (MHz) | Ppeak(dBm) | ACPR (dBc) | Gain (dB) | EFF (%) |
| 5900 | 45.93 | -30.7 | 23.3 | 37.8 |
| 6000 | 45.88 | -31.4 | 23.2 | 37.7 |
| 6100 | 45.7 | -32 | 23.1 | 37.6 |

• Notes:

(1) WCDMA signal: 3GPP test model 1; 1 to 64 DPCH; Channel Bandwidth=3.84MHz, PAR =10.5 dB at 0.01 % probability on CCDF.

Features

- Industry leading RF performance for 5G MIMO AAU running at 6GHz, for instance
 - ✓ 64T:200W/ 200MHz
- Plastic open cavity without molding compound brings advantage compared to molded design
 - ✓ Minimize the risk of high density thermal distribution in fanless system for longer life time
 - ✓ Highly consistent RF performance for yield of volume production
- 50 Ω Input/output matched,
- Integrated Doherty Final and driver Stage
- 6x10 mm Surface Mount Package, full copper flange underneath for grounding and heat dissipation
- **When biased as Class AB, it can be extended as 5-6GHz 35W PA as well**

Pin Configuration and Description





| Pin No. | Symbol | Description |
|---|--------|--|
| 1 | VD1 | Driver Amplifier, Drain Bias |
| 3 | VG1 | Driver Amplifier, Gate Bias |
| 6 | RF IN | RF Input |
| 11 | VG3 | Carrier Amplifier, Gate Bias |
| 16 | BE | VBW Enhance |
| 22 | RF OUT | RF Output |
| 27 | VD2 | Peaking Amplifier, Drain Bias |
| 32 | VG2 | Peaking Amplifier, Gate Bias |
| 4,8-10,14-15,17,19,21,24,26,28,29,33-35 | NC | No connection |
| 2,5,7,12,13,18,20,23,25,30,31,36 | GND | Internal Grounding, recommend connecting to Epad ground |
| Package Base | GND | DC/RF Ground. Must be soldered to EVB ground plane over array of vias for thermal and RF performance. Solder voids under Pkg Base will result in excessive junction temperatures causing permanent damage. |

Table 1. Maximum Ratings

| Rating | Symbol | Value | Unit |
|--------------------------------|-----------|-------------|------|
| Drain--Source Voltage | V_{DSS} | 200 | Vdc |
| Gate--Source Voltage | V_{GS} | -8 to +0.6 | Vdc |
| Operating Voltage | V_{DD} | +55 | Vdc |
| Storage Temperature Range | T_{stg} | -65 to +150 | °C |
| Case Operating Temperature | T_c | +150 | °C |
| Operating Junction Temperature | T_j | +225 | °C |

Table 2. Thermal Characteristics

| Characteristic | Symbol | Value | Unit |
|--|-----------------|-------|------|
| Thermal Resistance@Average Power, Junction to Case Tcase=+85°C, CW Test, Pout=5.6W, | $R_{\theta JC}$ | TBD | °C/W |

Notes:

- (1) The thermal resistance is acquired by our company's FEA model, which was calibrated by IR measurement, the value shall be applied to reliability.
- (2) The reference Tcase temperature 85°C is apply on the backside of package.
- (3) If the device soldering onto the 20mil Rogers PCB with $50 \times \Phi 0.4$ mm via hole beneath the package backside and the reference temperature Tcase (85°C) apply on the groundside of the PCB, the total thermal resistance $R_{\theta JC}$ (TBD)°C/W.
- (4) The power dissipation in the table is overall dissipation which include Carrier PA, Peaking PA and driver PA.

Table 3. ESD Protection Characteristics

| Test Methodology | Class Voltage |
|--|---------------|
| Human Body Model(HBM) (JEDEC Standard JESD-A114) | TBD |
| Charged Device Model (CDM) (JEDEC Standard JESD22-C101F) | ±1000V |

Table 4: Load Mismatch Characteristics (On Test Fixture, 50 ohm system): f = 6.0 GHz

| | |
|---|-----------------------|
| VSWR 10:1 at P3dB pulse CW Output Power | No Device Degradation |
|---|-----------------------|

Reference Circuit of Test Fixture Assembly Diagram

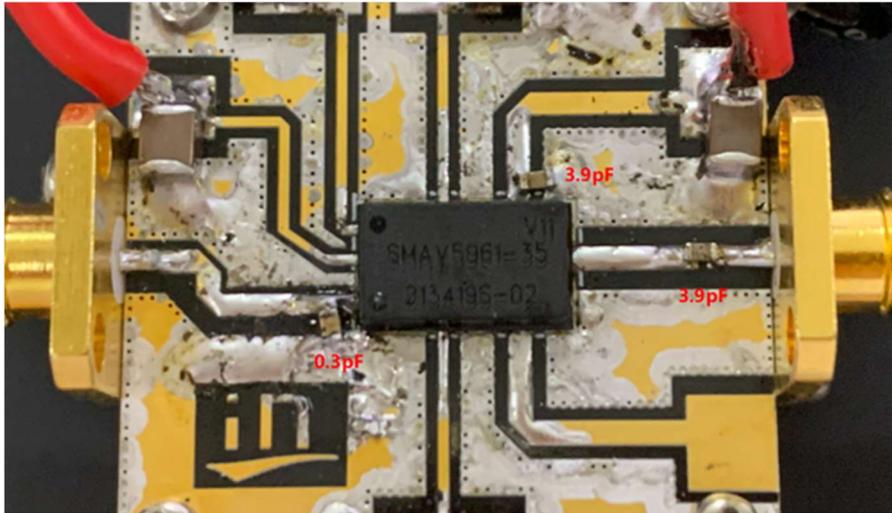


Figure 1. Test Circuit Component Layout

TYPICAL CHARACTERISTICS

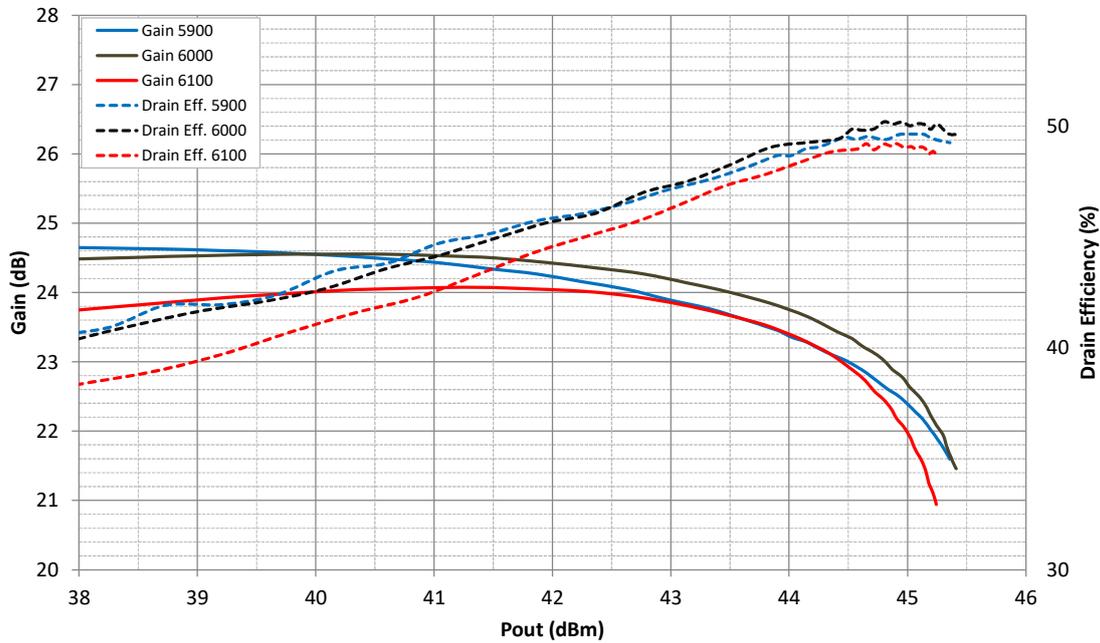


Figure 2. Power Gain and Drain Efficiency as Function of Pulsed CW Output Power

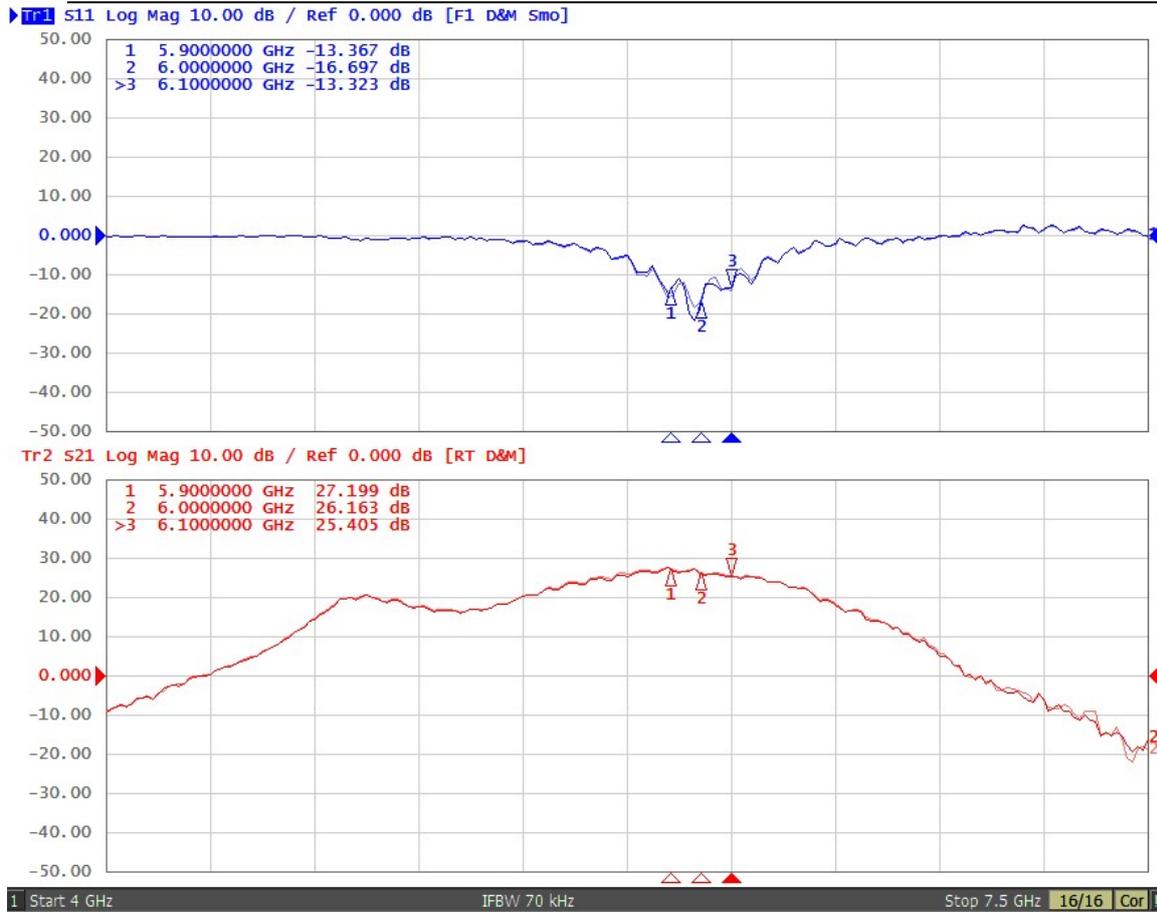
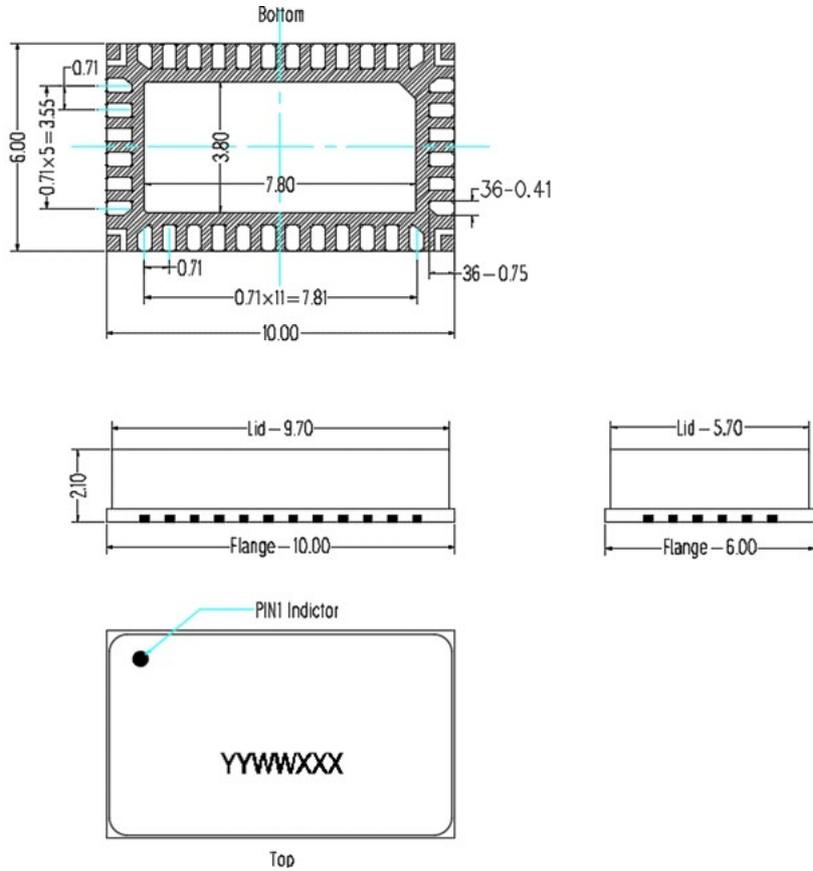


Figure 3. Network analyzer output, S11/S21



Package Dimensions

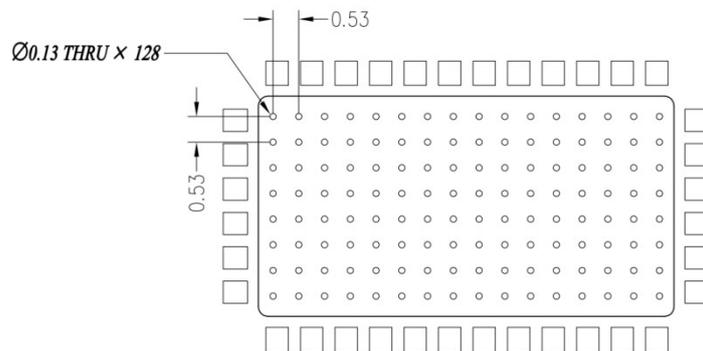
10*6 Plastic Package



Notes:

1. All dimensions are in mm;
2. The tolerances unless specified are ± 0.2 mm.

Mounting Footprint Pattern



Notes:

1. All dimensions are in mm;
2. Vias are required under the backside paddle of this device for proper RF/DC grounding and thermal dissipation. ALL vias are PTH to ground.



Revision history

Table 4. Document revision history

| Date | Revision | Datasheet Status |
|-----------|----------|--|
| 2021/8/23 | Rev 1.0 | Preliminary Datasheet |
| 2021/8/20 | Rev 1.1 | SMAV to SMBV and update according to latest application report |
| 2022/9/10 | Rev 1.2 | Correct typo of pin definition, VG1 and RF OUT |
| | | |

Application data based on HJ-21-12

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